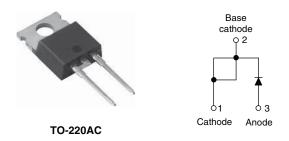


**Vishay Semiconductors** 

# Ultrafast Rectifier, 15 A FRED Pt®



PRODUCT SUMMARY							
Package	TO-220AC						
I <sub>F(AV)</sub>	15 A						
V <sub>R</sub>	200 V						
V <sub>F</sub> at I <sub>F</sub>	0.85 V						
t <sub>rr</sub> typ.	See Recovery table						
T <sub>J</sub> max.	175 °C						
Diode variation	Single die						

## **FEATURES**

- Ultrafast recovery time
- Low forward voltage drop
- 175 °C operating junction temperature
- Low leakage current
- Designed and qualified according to JEDEC<sup>®</sup>-JESD 47



ROHS COMPLIANT HALOGEN FREE Available

 Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

## **DESCRIPTION / APPLICATIONS**

VS-MUR1520PbF is the state of the art ultrafast recovery rectifier specifically designed with optimized performance of forward voltage drop and ultrafast recovery time.

The planar structure and the platinum doped life time control, guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, UPS, DC/DC converters as well as freewheeling diode in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS									
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS					
Peak repetitive reverse voltage	V <sub>RRM</sub>		200	V					
Average rectified forward current	I <sub>F(AV)</sub>	Total device, rated V <sub>R</sub> , T <sub>C</sub> = 150 °C	15						
Non-repetitive peak surge current	I <sub>FSM</sub>		200	А					
Peak repetitive forward current	I <sub>FM</sub>	Rated V <sub>R</sub> , square wave, 20 kHz, $T_C = 150 \text{ °C}$	30						
Operating junction and storage temperatures	T <sub>J</sub> , T <sub>Stg</sub>		-65 to +175	°C					

<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)										
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS				
Breakdown voltage, blocking voltage	V <sub>BR</sub> , V <sub>R</sub>	I <sub>R</sub> = 100 μA	200	-	-					
Forward voltage	V <sub>F</sub>	I <sub>F</sub> = 15 A -		-	1.05	V				
		I <sub>F</sub> = 15 A, T <sub>J</sub> = 150 °C	-	-	0.85					
Reverse leakage current	I <sub>R</sub>	V <sub>R</sub> = V <sub>R</sub> rated	-	-	10					
		$T_J = 150 \text{ °C}, V_R = V_R \text{ rated}$	-	-	500	μA				
Junction capacitance	CT	V <sub>R</sub> = 200 V	-	55	-	pF				
Series inductance	L <sub>S</sub>	Measured lead to lead 5 mm from package body	-	8.0	-	nH				

 Revision: 18-Jun-15
 1
 Document Number: 94077

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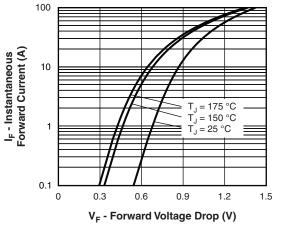
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<b>DYNAMIC RECOVERY CHARACTERISTICS</b> ( $T_J = 25$ °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS			
Reverse recovery time		$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t =$	$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t = 50 \text{ A}/\mu\text{s}, V_R = 30 \text{ V}$		-	35			
	t <sub>rr</sub>	T <sub>J</sub> = 25 °C		-	22	-	ns • A		
		T <sub>J</sub> = 125 °C		-	39	-			
Dook rooovon ( ourront	I <sub>RRM</sub>	T <sub>J</sub> = 25 °C	$I_F = 15 A$	-	1.6	-			
Peak recovery current		T <sub>J</sub> = 125 °C	dl <sub>F</sub> /dt = 200 A/µs V <sub>B</sub> = 160 V	-	4.1	-			
Reverse recovery charge	0	T <sub>J</sub> = 25 °C		-	19	-			
	Q <sub>rr</sub>	T <sub>J</sub> = 125 °C		-	90	-	nC		

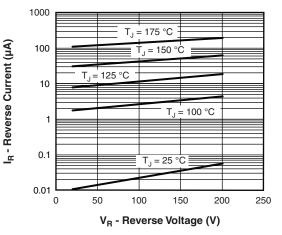
THERMAL - MECHANICAL SPECIFICATIONS										
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS				
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-65	-	175	°C				
Thermal resistance, junction to case	R <sub>thJC</sub>		-	-	1.5					
Thermal resistance, junction to ambient	R <sub>thJA</sub>		-	-	50	°C/W				
Thermal resistance, case to heatsink	R <sub>thCS</sub>	Mounting surface, flat, smooth and greased	-	0.5	-					
Weight			-	2.0	-	g				
Weight			-	0.07	-	OZ.				
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)				
Marking device		Case style TO-220AC	MUR1520							

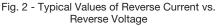
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Fig. 1 - Typical Forward Voltage Drop Characteristics





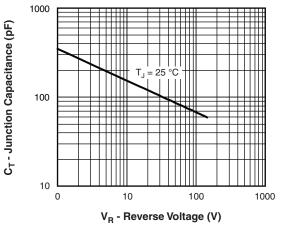


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

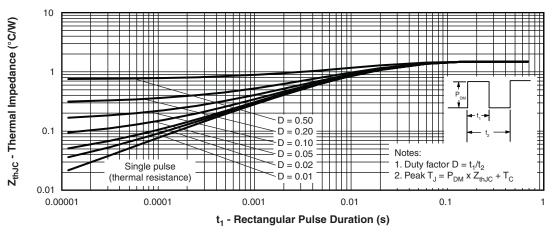
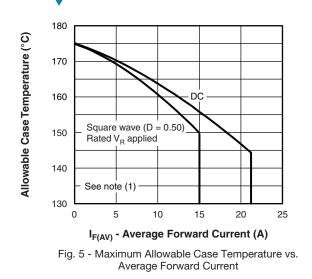


Fig. 4 - Maximum Thermal Impedance Z<sub>thJC</sub> Characteristics

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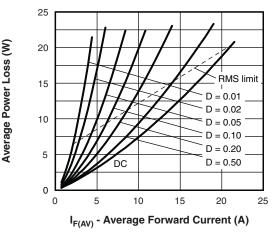
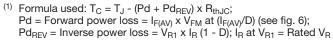


Fig. 6 - Forward Power Loss Characteristics

#### Note



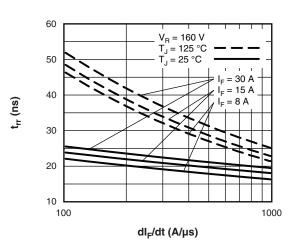


Fig. 7 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt

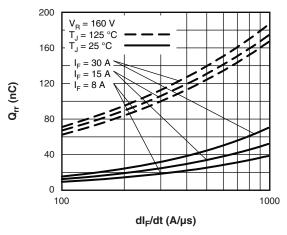


Fig. 8 - Typical Stored Charge vs. dl<sub>F</sub>/dt



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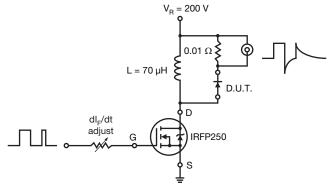
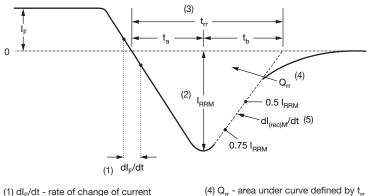


Fig. 9 - Reverse Recovery Parameter Test Circuit



- (1) dI<sub>F</sub>/dt rate of change of current through zero crossing
- (2) I<sub>RRM</sub> peak reverse recovery current
- (3)  $t_{rr}$  reverse recovery time measured from zero crossing point of negative going  $I_F$  to point where a line passing through 0.75  $I_{RRM}$  and 0.50  $I_{RRM}$ extrapolated to zero current.
- and I<sub>RRM</sub>

$$Q_{\rm rr} = \frac{t_{\rm rr} \times I_{\rm RRM}}{2}$$

- (5) dl\_{(rec)M}/dt peak rate of change of current during  $t_{\rm b}$  portion of  $t_{\rm rr}$
- Fig. 10 Reverse Recovery Waveform and Definitions

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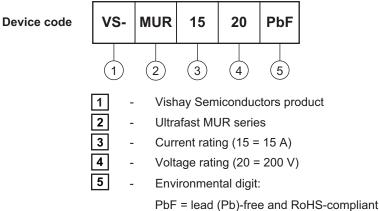
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## **ORDERING INFORMATION TABLE**



-N3 = halogen-free, RoHS-compliant and totally lead (Pb)-free

ORDERING INFORMATION (Example)									
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION						
VS-MUR1520PbF	50	1000	Antistatic plastic tube						
VS-MUR1520-N3	50	1000	Antistatic plastic tube						

LINKS TO RELATED DOCUMENTS							
Dimensions		www.vishay.com/doc?95221					
Part marking information	TO-220ACPbF	www.vishay.com/doc?95224					
Fart marking information	TO-220AC-N3	www.vishay.com/doc?95068					
SPICE model		www.vishay.com/doc?95271					



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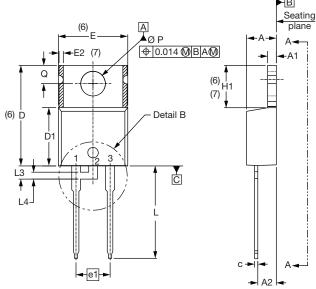
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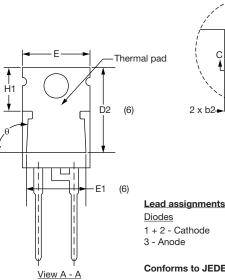
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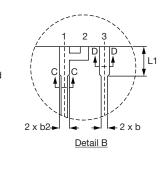
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plane

### **DIMENSIONS** in millimeters and inches









**Diodes** 1 + 2 - Cathode 3 - Anode

Conforms to JEDEC outline TO-220AC

⊕ 0.015 **()** BA()

SYMBOL	MILLIM	IETERS	INCHES		NOTES	SYMBOL	MILLIN	IETERS	INCHES		NOTES	
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES	STWIDOL	MIN.	MAX.	MIN.	MAX.	NOTES	
А	4.25	4.65	0.167	0.183			E1	6.86	8.89	0.270	0.350	6
A1	1.14	1.40	0.045	0.055			E2	-	0.76	-	0.030	7
A2	2.56	2.92	0.101	0.115			е	2.41	2.67	0.095	0.105	
b	0.69	1.01	0.027	0.040			e1	4.88	5.28	0.192	0.208	
b1	0.38	0.97	0.015	0.038	4		H1	6.09	6.48	0.240	0.255	6, 7
b2	1.20	1.73	0.047	0.068			L	13.52	14.02	0.532	0.552	
b3	1.14	1.73	0.045	0.068	4		L1	3.32	3.82	0.131	0.150	2
С	0.36	0.61	0.014	0.024			L3	1.78	2.13	0.070	0.084	
c1	0.36	0.56	0.014	0.022	4		L4	0.76	1.27	0.030	0.050	2
D	14.85	15.25	0.585	0.600	3		ØΡ	3.54	3.73	0.139	0.147	
D1	8.38	9.02	0.330	0.355			Q	2.60	3.00	0.102	0.118	
D2	11.68	12.88	0.460	0.507	6		θ	90° t	o 93°	90° t	o 93°	
E	10.11	10.51	0.398	0.414	3, 6							

Notes

<sup>(1)</sup> Dimensioning and tolerancing as per ASME Y14.5M-1994

<sup>(2)</sup> Lead dimension and finish uncontrolled in L1

(3) Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body

- <sup>(4)</sup> Dimension b1, b3 and c1 apply to base metal only
- <sup>(5)</sup> Controlling dimension: inches
- <sup>(6)</sup> Thermal pad contour optional within dimensions E, H1, D2 and E1
- <sup>(7)</sup> Dimension E2 x H1 define a zone where stamping and singulation irregularities are allowed
- <sup>(8)</sup> Outline conforms to JEDEC TO-220, D2 (minimum) where dimensions are derived from the actual package outline

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